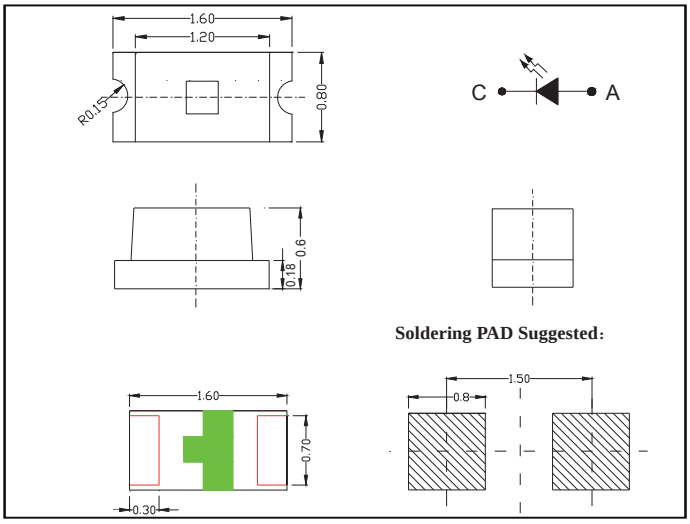
HFZT

SMD 0603普绿

Light Emitting Diode

Features

- ●Package (L/W/H) : 1.6 × 0.8 × 0.6 mm
- ●Color : Yellow Green
- ●Lens: Water Clear Flat Mold
- ●EIA STD Package
- ●Meet ROHS, Green Product
- ●Compatible With SMT Automatic Equipment
- ●Compatible With Infrared Reflow Solder And Wave Solder Process



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Power Dissipation	Pd	60	mW
Peak Forward Current (1/10 Duty Cycle, 0.1ms Pulse Width)	I_{FP}	30	mA
DC Forward Current	I_F	20	mA
Reverse Voltage	V_R	5	V
Operating Temperature Range	Topr	-30°C ~ +85°C	
Storage Temperature Range	Tstg	-40°C ~ +90°C	
Soldering Condition	Tsol	Reflow soldering : 250°C For 5 Seconds Hand soldering: 300°C For 3 Seconds	

Electrical Specification (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Luminous Intensity	IV	30	40	50	mcd	IF = 20mA
Viewing Angle	2θ1/2	---	120	---	deg	IF = 20mA
Dominant Wavelength	λd	---	570	---	nm	IF=20mA
Peak Wavelength	λp	---	575	---	nm	IF=20mA
Spectral Line Half-Width	Δλ	---	15	---	nm	IF=20mA
Forward Voltage	VF	1.8	2.0	2.4	V	IF=20mA
Reverse Current	IR	---	---	10	uA	VR=5V

Notes: 1. Luminous intensity is measured with a light sensor and filter combination that approximates the CIE eye-response curve.
2. θ1/2 is the off-axis angle at which the luminous intensity is half the axial luminous intensity.
3. The dominant wavelength, λd is derived from the CIE chromaticity diagram and represents the single wavelength which defines the color of the device.

RATINGS AND CHARACTERISTIC CURVES

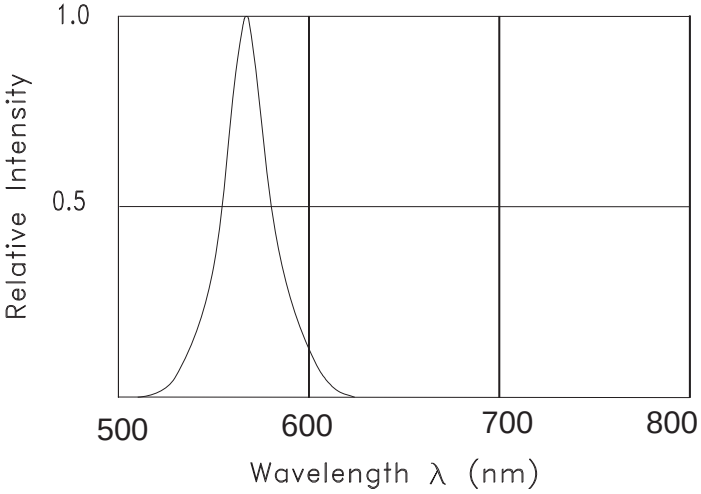


Fig.1 RELATIVE INTENSITY VS. WAVELENGTH

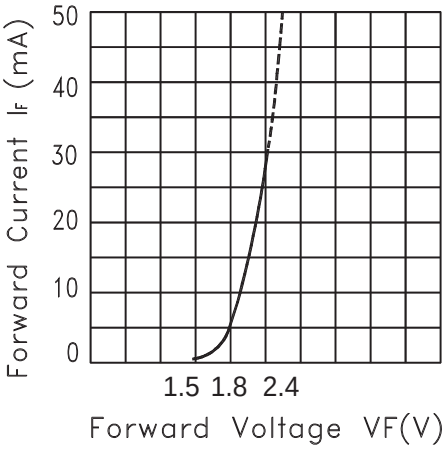


Fig.2 FORWARD CURRENT VS. FORWARD VOLTAGE

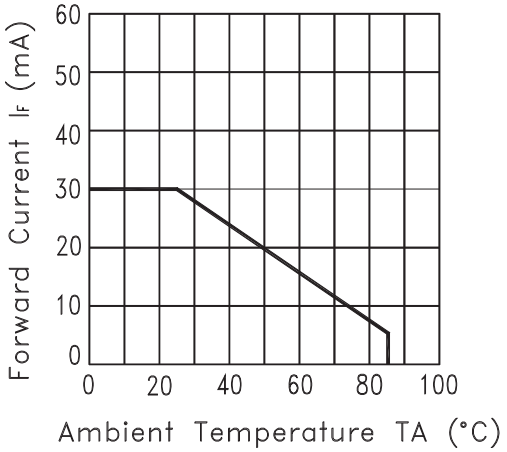


Fig.3 FORWARD CURRENT DERATING CURVE

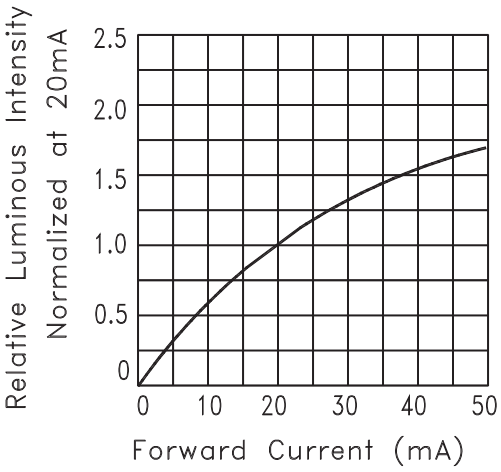


Fig.4 RELATIVE LUMINOUS INTENSITY VS. FORWARD CURRENT

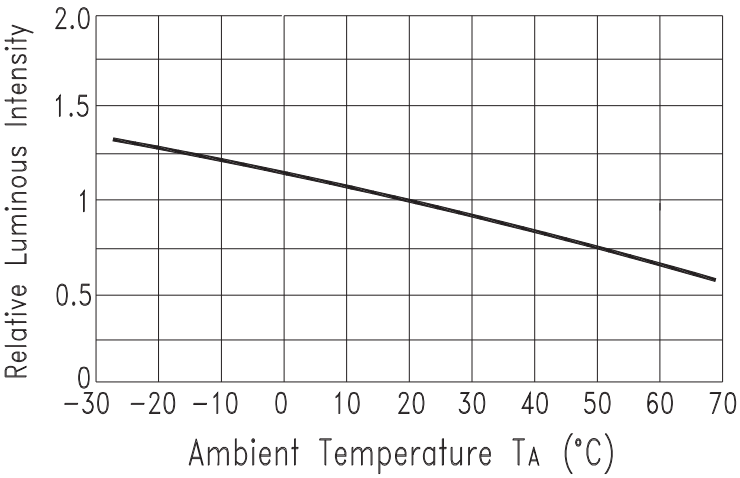


Fig.5 Luminous Intensity vs.Ambient Temperature

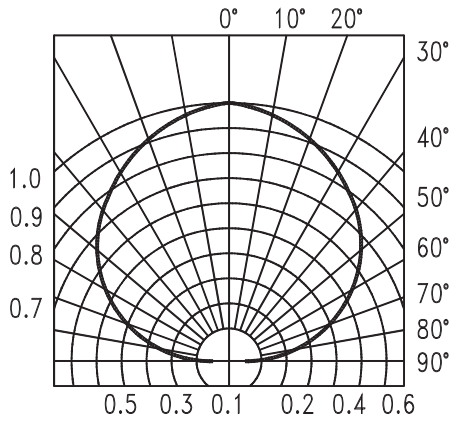


Fig.6 SPATIAL DISTRIBUTION